



SLOVENSKI STANDARD
oSIST prEN IEC 61189-2-808:2023
01-april-2023

Preskusne metode za električne materiale, tiskana vezja in druge povezovalne strukture in sestave - 2-808. del: Meritev toplotne upornosti sestava z metodo toplotnega prehajanja

Test methods for electrical materials, printed board and other interconnection structures and assemblies - Part 2-808: Thermal resistance of an assembly by thermal transient method

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TITLE:

Test methods for electrical materials, printed board and other interconnection structures and assemblies – Part 2-808: Thermal resistance of an assembly by thermal transient method

PROPOSED STABILITY DATE: 2028

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**Test methods for electrical materials, printed board and other
interconnection structures and assemblies – Part 2-808: Thermal
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82 International Standard IEC 61189-2-808 Ed. 1 has been prepared by IEC technical committee
83 TC91: Electronics assembly technology.

84 The text of this International Standard is based on the following documents:

FDIS	Report on voting
XX/XX/FDIS	XX/XX/RVD

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Full information on the voting for the approval of this International Standard can be found in the report on voting indicated in the above table.

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- 92 • reconfirmed,
93 • withdrawn,
94 • replaced by a revised edition, or
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96

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98 is 2028..

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105 **Test methods for electrical materials, printed board and other**
106 **interconnection structures and assemblies – Part 2-808: Thermal**
107 **resistance of an assembly by thermal transient method**
108

109 **1 Scope**

110 This document describes the thermal transient method to characterize the thermal resistance
111 of an assembly consisting of a heat source (e.g. power device), an attachment material (e.g.
112 solder) and a dielectric layer with electrode. It is suitable to determine the thermal resistance
113 of materials and assembly methods as well as to optimize the thermal flux to a heat sink.
114

115 Note: This method is not intended to measure and specify the value of the thermal resistance
116 of a dielectric material. For that purpose, other standards exist. Examples are given in Annex
117 A.

118 **2 Normative references**

119 JESD51-14 Transient Dual Interface Test Method

120 **3 Terms and Definitions**

121 For the purposes of this document, the terms and definitions given in IEC 60194-2 and the
122 following apply.

123 ISO and IEC maintain terminological databases for use in standardization at the following
124 addresses:

125 • IEC Electropedia: available at <http://www.electropedia.org/>

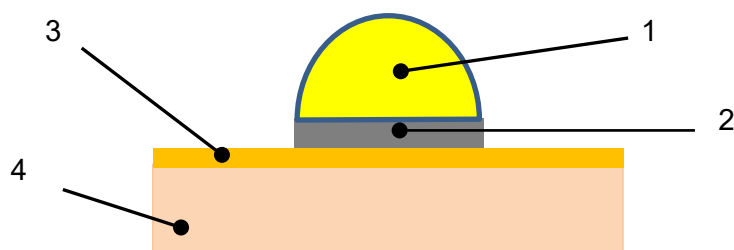
126 • ISO Online browsing platform: available at <http://www.iso.org/obp>

127 **4 Objective**

128 The increasing power consumption of devices such as LED require a close examination of the
129 heat dissipating path within thermal conductive printed circuit boards. Therefore, effective
130 removal of heat to maintain a safe junction temperature is the key to meet the heat flux by using
131 thermal conductive material for printed circuit boards. Thermal resistance is the crucial factor
132 of heat dissipation dielectric materials in printed circuit board. Therefore, with the aim to reduce
133 the thermal resistance in circuit boards, it is proposed to determine the thermal resistance by
134 measuring the thermal transient characteristics of an assembly.

135 **5 Test specimen**

136 To test the thermal resistance of an assembly, at first a test specimen shall be built, which
137 consists of a heat source (e.g. power device), an attachment material (e.g. solder) and a
138 dielectric layer with metal electrode. See Figure 1 for the structure. In the next step, the thermal
139 resistance of the assembly can be determined by comparison of the thermal transient
140 characteristics obtained when testing the assembly attached to a thermostat with or without a
141 thermal interface material (TIM). See Figure 3 and Clause 6 for the test description.



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1	Power source
2	Solder
3	Electrode layer
4	Dielectric layer

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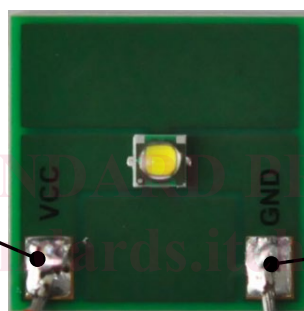
Figure 1 – Structure of an assembly

150 To obtain an adequate thermal resistance a layer of around 200 µm thick solder shall be used
 151 for die attach. The power source is a chip type device of the size 3,45 mm x 3,45 mm, powered
 152 with 1 W through VCC and GND. The dielectric layer is a 2 cm x 2 cm substrate of 1 mm
 153 thickness. Figure 2 shows the example of such a test specimen.

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155

1	VCC
2	GND



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Figure 2 – The fabricated test sample

158 6 Test equipment and procedures

159 6-1 Test method and recommended test parameters

160 The thermal transient test equipment is a unique equipment for performing thermal
 161 measurements on semiconductor devices like ICs, transistors, diodes etc. The thermal transient
 162 test equipment is most suitable for analyzing their thermal behavior, evaluating packages and
 163 device mounting, and detecting defects. This equipment is a computer-controlled equipment
 164 that can be used along with a PC hosting a special control and evaluation software. This
 165 equipment as a mandatory part of configuration can apply programmed thermal excitations and
 166 record complex thermal responses and provides built-in results evaluation procedures. Results
 167 of these post-processing procedures include the pulse thermal resistance diagram, time-
 168 constant spectrum, complex locus of the thermal impedance, differential and integral structure
 169 or profile function.

170 6-2 Test equipment

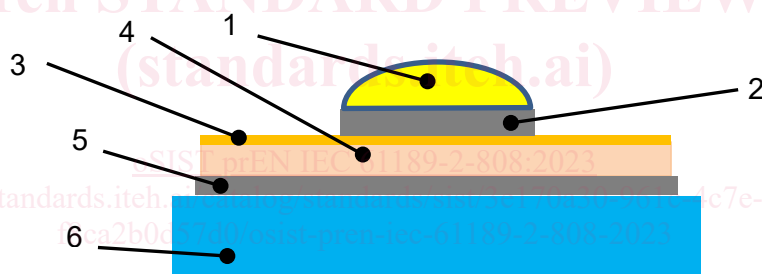
171 The thermal transient measurements can be performed using a commercially available test
 172 equipment T3ster¹ and specifically built test fixtures. Test sample is mounted on the
 173 temperature-controlled heat sink. The heat sink is maintained at a temperature of 25°C and
 174 controlled by a Keithley temperature controller. Initially, a junction-to-case thermal equilibrium
 175 is ensured by applying a drive current (I_{drive}) for a sufficiently long duration; then the I_{drive} is
 176 switched off and a small sense current (I_{sense}) is applied. When the system shifts to its new
 177 thermal equilibrium, the cooling down of the junction is measured.

178 1 T3ster[®] equipment is the trademark of a product supplied by MICRED (now Mentor Graphics).
 179 This information is given for the convenience of users of this document and does not constitute

180 an endorsement by IEC of the product named. Equivalent products may be used if they can be
 181 shown to lead to the same results.

182 From the transient time curves, the duration of cooling down can be taken for how long the
 183 heating current Idrive needs to be applied to load the thermal capacities. The same time must
 184 be measured applying Isense to resolve the thermal path downstream to the respective capacity.
 185 One approach to determine the required measurement time is to modify the thermal interface
 186 between the heat sink and the module. The time value at which the curve with the best possible
 187 thermal interface and one with bad thermal interface separate is approximately the appropriate
 188 time duration for Idrive and Isense when the thermal path upstream the varied thermal interface
 189 is to be investigated. One can stepwise shorten the heat-up and cool down time afterward and
 190 observe at what setting, and at which time, values change in the logarithmic time-derived curve.
 191 The shortest time for which the deviation of the time curves is still within the signal-to-noise
 192 range of the curve with long heating and cooling times is still acceptable. The thermal response
 193 at initial '0' cycles and after 'n' cycles was measured. The measurement time of 40s is
 194 unnecessarily long. For the second test run with test samples B the measurement time was
 195 reduced to 5s. In principle, this allowed us to reduce the heating up and cooling down time
 196 further to 0.5s, because data later than 300ms are not included for data analysis. The shape of
 197 the transient signal does not change when cycle of heating up and cooling down times is
 198 shortened. In this experimental, the thermal tape (Thermal conductivity: 6.5 W/mK) with the
 199 thickness of 500 μm is used. Thermal tape as thermal interface material is used for separating
 200 the interface of the test sample through the comparison of thermal transient characteristics
 201 depending on with or without thermal interface material.

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1	Power source (1W)
2	SAC305 solder (T: 200um)
3	Electrode layer (T: 35um)
4	Dielectric layer (T: 500um)
5	Thermal interface material (T: 500um)
6	Thermostat

214 **Figure 3 – Test structure for measuring thermal resistance**

- 215 ● Noted: Thermostat is the temperature-controlled system (Annex D). Thermostat has the
 216 thermocouples inside system.

217 6-3 Test procedure

218 The test sequences to test the thermal resistance of an assembly are as follows.

- 219 1) Cleaning the contamination on the thermostat.
- 220 2) Firstly, attaching the test sample on the thermostat without the thermal interface
 221 material.
- 222 3) Testing the thermal transient characteristics of the test sample by biasing the power.

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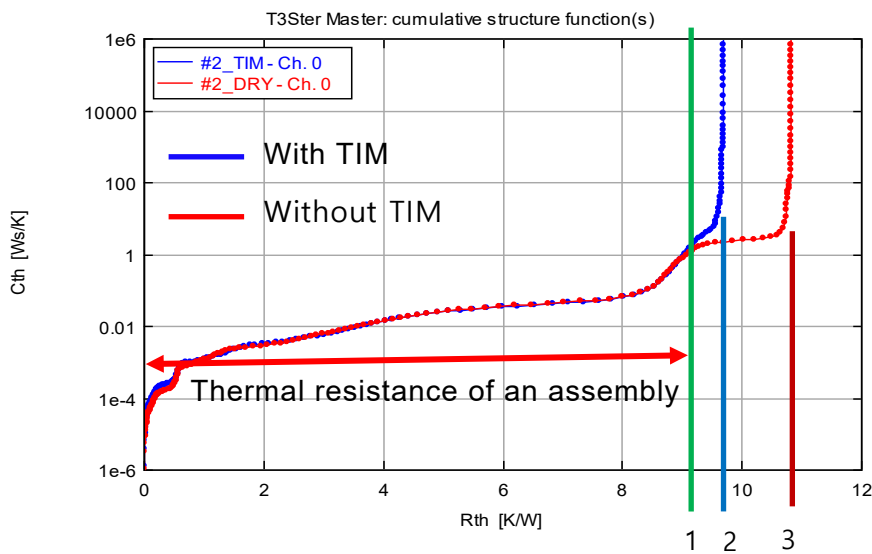
- Driving Current (I_{drive}): 1500 mA
- Sensor Current (I_{sense}) for Test: 10 mA
- Total Power: 4.548 W
- TIM: Thermal pad (Thickness: 500um)
- Temperature Coeff.: -1.272 mV/°C

- 231 4) Repeat the sequence 1).
- 232 5) Secondly, attaching the test sample on the thermostat by using thermal interface
233 material.
- 234 6) Testing the thermal transient characteristics of the test sample by biasing the power.
- 235 7) Comparing the thermal transient characteristics of the test sample depending on with
236 or without the thermal interface material.
- 237 8) Extracting the thermal resistance value of an assembly with test results.

238 **7 Test result**

239 From the cumulative structure function of the thermal transient characteristics after converting
240 to the cumulative structure function because it is eased to look for the separation point, the
241 thermal resistance value is extracted by looking for the separated point from the measurement
242 excel sheet instead of the visible graph (see Figure 4 and Table 1). It needs to refer to the
243 standards of JESD-51-14 clause 4 Junction-to-Case Thermal Resistance Measurement (Test
244 Method) for the detailed information.

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1	The measured of thermal resistance of an assembly
2	The measured thermal resistance of assembly without TIM
3	The measured thermal resistance of assembly with TIM

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267 **Figure 4 – Test result for thermal resistance of an assembly**

268 Note: Cth is thermal capacitance and K is temperature (Kelvin).

269 Note: In order to extract value for thermal resistance of assembly, it should look for the
270 separated value from the measurement results depending on with TIM and without TIM.

271 **Table 1 – Test result for thermal resistance of an assembly**

Total thermal resistance (without TIM), K/W	Total thermal resistance (with TIM), K/W	Thermal resistance of an assembly, K/W
10.86	9.68	9.2

272

273 **8 Report**

274 This test method shall include:

275

276 a) structure of test specimen

277 b) thermal tape used as TIM.

278 c) the used power sources.

279 d) the date of the test.

280 e) the room temperature under which the test was conducted.

281 f) the test sequences.

282 g) the graph of the cumulative structure function

283 h) the total thermal resistance of test specimen with or without TIM.

284 i) the thermal resistance of an assembly

285 Noted: The result value of an assembly separated differently from the measurement results
286 depending on the presence or absence of TIM is defined as the thermal resistance of and
287 assembly. It shall refer to JESD-51-14 clause 4 Junction-to-Case Thermal Resistance
288 Measurement (Test Method).

289 **9 Bibliographies**

290 JESD51-14 Transient Dual Interface Test Method

291

292 JESD-51-50: Overview of Methodologies for the Thermal Measurement of Single- and Multi-
293 Chip, Single- and Multi-PN-Junction Light-Emitting Diodes (LEDs)

294

295 JESD-51-51: Implementation of the Electrical Test Method for the Measurement of the Real
296 Thermal Resistance and Impedance of Light-emitting Diodes with Exposed Cooling Surface

297

298 JEDEC Solid State Technology Association (JEDEC Standard)

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300 JEDEC JESD51-1: INTEGRATED CIRCUIT THERMAL MEASUREMENT METHOD -
301 ELECTRICAL TEST METHOD (SINGLE SEMICONDUCTOR DEVICE):

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